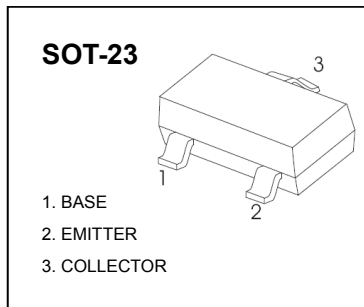
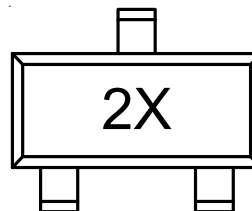


MMBT4401: Switching transistor(NPN)

Pin Configuration



Marking Information



2X = Device Marking Code

Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

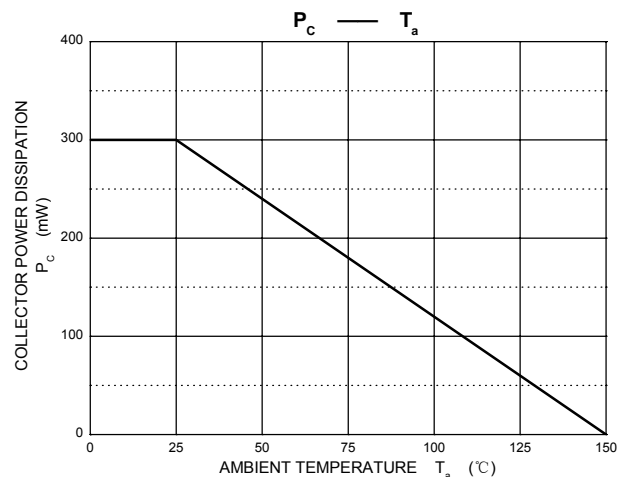
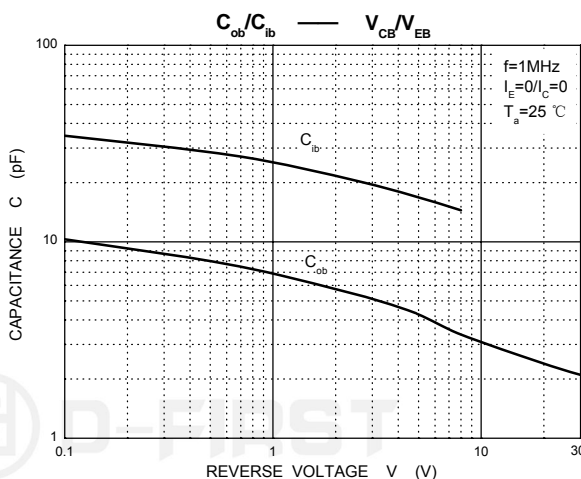
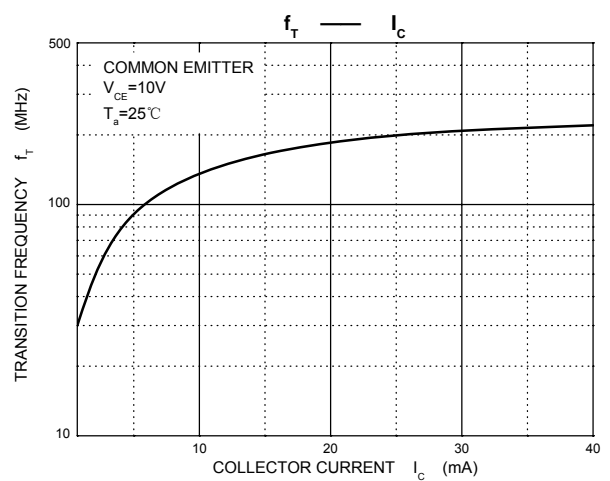
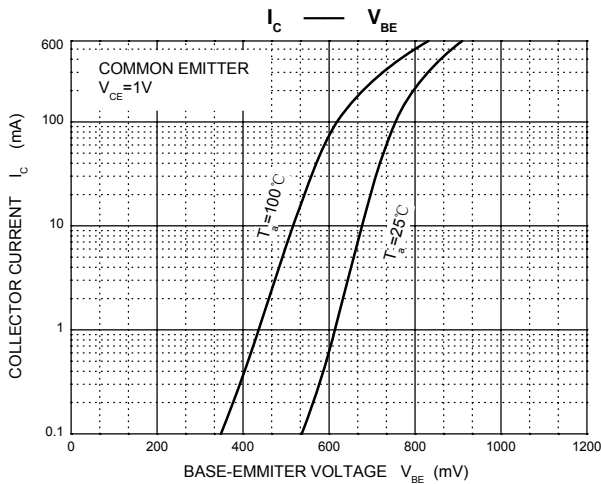
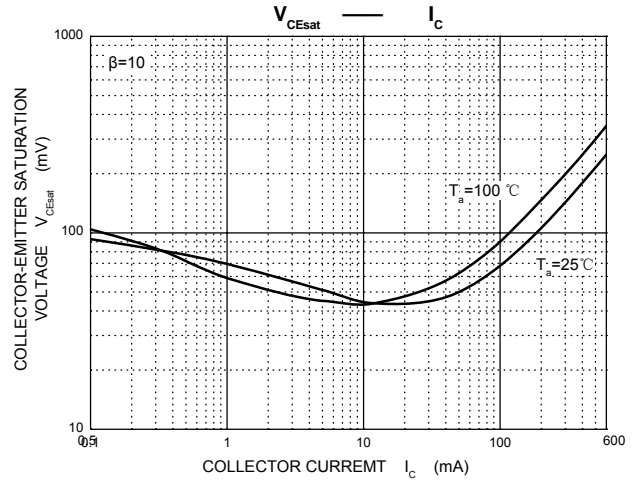
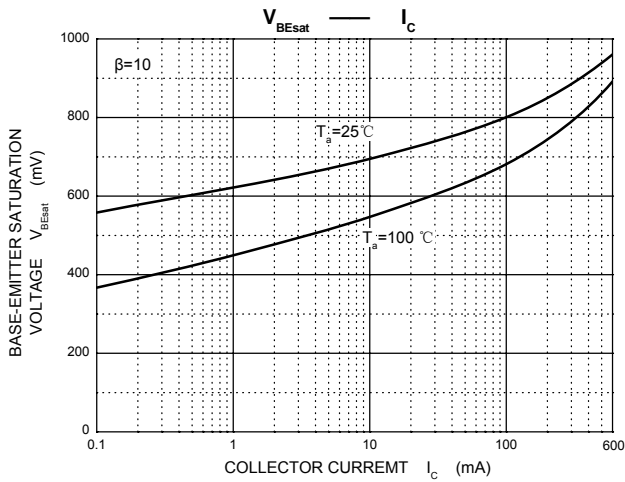
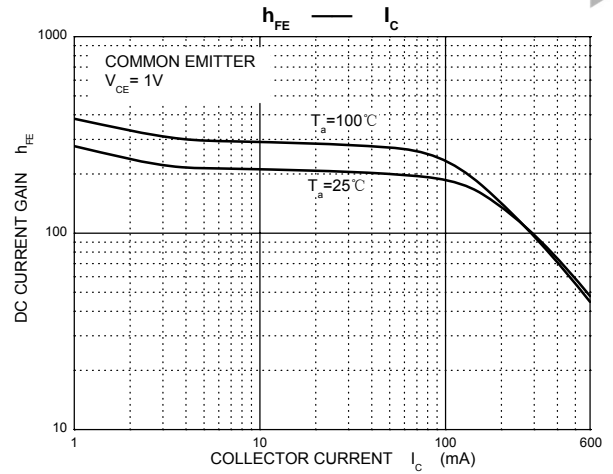
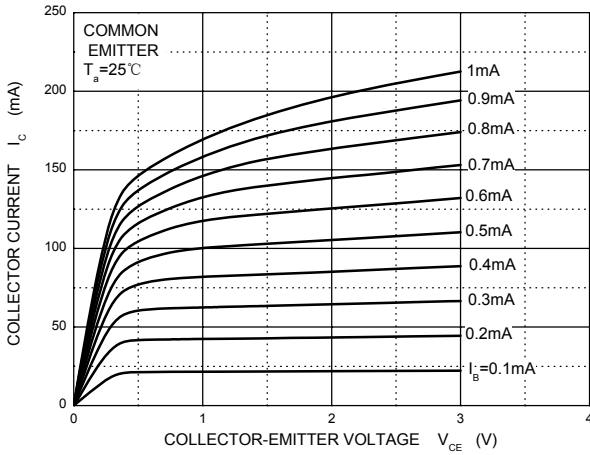
Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	40	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current	600	mA
P_C	Collector Power Dissipation	300	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	417	$^{\circ}\text{C}/\text{W}$
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^{\circ}\text{C}$

Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

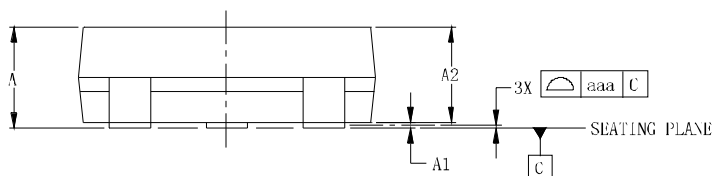
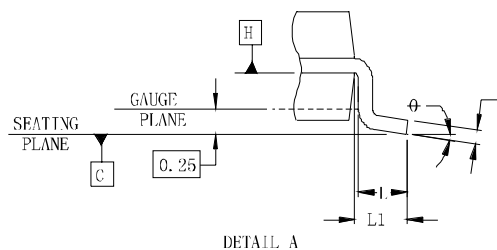
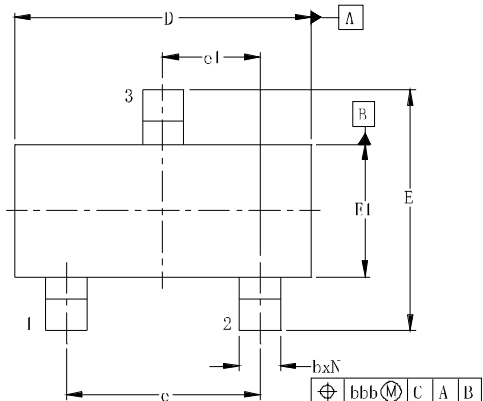
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\ \mu\text{A}, I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	40			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\ \mu\text{A}, I_C=0$	6			V
Collector cut-off current	I_{CBO}	$V_{CB}=50\text{V}, I_E=0$			0.1	μA
Collector cut-off current	I_{CEX}	$V_{CE}=35\text{V}, V_{EB}=0.4\text{V}$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5\text{V}, I_C=0$			0.1	μA
DC current gain	h_{FE1}	$V_{CE}=1\text{V}, I_C=0.1\text{mA}$	20			
	h_{FE2}	$V_{CE}=1\text{V}, I_C=1\text{mA}$	40			
	h_{FE3}	$V_{CE}=1\text{V}, I_C=10\text{mA}$	80			
	h_{FE4}	$V_{CE}=1\text{V}, I_C=150\text{mA}$	100		300	
	h_{FE5}	$V_{CE}=2\text{V}, I_C=500\text{mA}$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=150\text{mA}, I_B=15\text{mA}$			0.4	V
		$I_C=500\text{mA}, I_B=50\text{mA}$			0.75	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=150\text{mA}, I_B=15\text{mA}$			0.95	V
		$I_C=500\text{mA}, I_B=50\text{mA}$			1.2	V
Transition frequency	f_T	$V_{CE}=10\text{V}, I_C=20\text{mA}, f=100\text{MHz}$	250			MHz
Delay time	t_d	$V_{CC}=30\text{V}, V_{BE(off)}=-2\text{V}$			15	ns
Rise time	t_r	$I_C=150\text{mA}, I_{B1}=15\text{mA}$			20	ns
Storage time	t_s	$V_{CC}=30\text{V}, I_C=150\text{mA}$			225	ns
Fall time	t_f	$I_{B1}=I_{B2}=15\text{mA}$			60	ns

Typical Performance Characteristics (TA=25°C unless otherwise Specified)

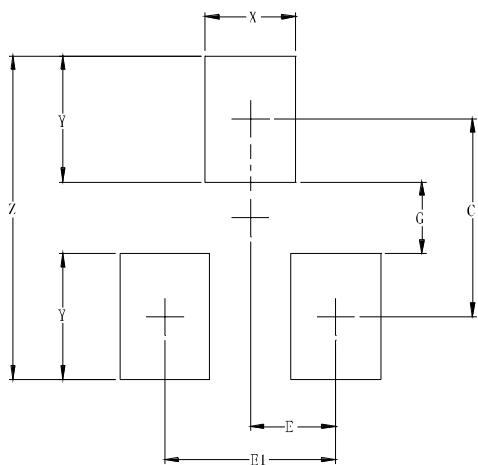
Static Characteristic



SOT-23 Package Outline Drawing



Suggested Land Pattern



Contact Information

Changzhou D-first Electronics CO.,Ltd.
 www.first-electronic.com
 Email: xhf@first-electronic.cn
 Phone: +86 (0519) 8817 1671

DIMENSIONS						
SYM	INCHES			MILLIMETERS		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.035	-	0.044	0.89	-	1.12
A1	0.000	-	0.004	0.01	-	0.10
A2	0.035	0.037	0.040	0.88	0.95	1.02
b	0.012	-	0.020	0.30	-	0.51
c	0.003	-	0.007	0.08	-	0.18
D	0.110	0.114	0.120	2.80	2.90	3.04
E	0.082	0.093	0.104	2.10	2.37	2.64
E1	0.047	0.051	0.055	1.20	1.30	1.40
e	0.075			1.90BSC		
e1	0.037			0.95BSC		
L	0.015	0.020	0.024	0.40	0.50	0.60
L1	0.022			0.55		
N	3			3		
ϕ	0°	-	8°	0°	-	8°
aaa	0.004			0.10		
bbb	0.008			0.20		

DIMENSIONS		
SYM	INCHES	MILLIMETERS
C	0.087	2.20
E	0.037	0.95
E1	0.075	1.90
G	0.031	0.80
X	0.039	1.00
Y	0.055	1.40
Z	0.141	3.60